E3-238: Home Work 3 (Due 23/10/03)

(Design guideline: For the maximum slew rate, try and utilize entire static power budget to bias the first and second stage. I.e. you have a total of 100 μ A bias current budget. You can allocate 60 μ A to M5 and 30 μ A to M7. Use rest of the 10 μ A for MB1, MB2 branch and MB3, MB4, MB5 branch. Then use appropriate W and L for first and second stage to get required gain. Then use appropriate Cc and nulling transistor for pole splitting and zero cancellation).

Characterize the following parameters through SPICE simulation:

- A. Determine the systematic input offset voltage if any. (Note: If you use Vdd=3.3V and Vss=0V, then you should ideally get Vout=1.65V for Vin1=Vin2=1.65V. This is equivalent to putting Vdd=1.65V, Vss=-1.65V and then the ideal case would be Vout=0 for Vin1=Vin2=0V. In order to get the offset with Vdd=3.3V, use Vin1=1.65V and sweep Vin2 around this value to make Vout=0). For all the subsequent questions, bias the OP-AMP using external DC voltage to cancel this offset.
- B. Plot open loop differential gain versus frequency (both magnitude and phase plot) using AC simulation. What is the unity gain bandwidth and what is the phase margin through simulation? What is the frequency of the dominant pole?
- C. Plot open loop common mode gain and CMRR versus frequency
- D. Using pole-zero analysis obtain all the poles and zeros of the OP-AMP for "differential response". Is this consistent with the results obtained in 2?
- E. Characterize the step response of the OP-AMP and thereby obtain the slew-rate. Obtain the step response for the following step inputs at Vin2:
 - a. $1\mu V (b) 1mV (c) 1V$
- F. Obtain PSRR (as a function of frequency)
- G. Connect a variable capacitance load at the output of the OP-AMP. Find the C_L at which the phase margin vanishes to zero.

(Fig. 1 is in the second page)



2. Use the two stage OP-AMP designed in 1. for comparator application. Suppose that the NMOS input transistors have mismatch in their threshold voltage. The transistor M1 has 5% higher VTH0 than nominal and transistor M2 has 5% lower VTH0 than nominal. (Create two more SPICE model files for NMOS transistor CMOSN_SLOW and CMOSN_FAST corresponding to these two values of VTH0. All other

parameters will remain similar to nominal model. Then, in your SPICE input file, M1 and M2 must reference these new model files instead of nominal model file.).

When Vin2=1.65V, the comparator transfer function with respect to Vin1 will not be symmetric about 1.65V due to the transistor mismatch. Estimate the minimum input differential voltage that can be amplified correctly (for both Vin<1.65 case and Vin>1.65V case).

Use input series cancellation and then estimate the minimum input differential voltage that can be amplified correctly (for both Vin<1.65 case and Vin>1.65V case)

Use output series cancellation and then estimate the minimum input differential voltage that can be amplified correctly (for both Vin<1.65 case and Vin>1.65V case)

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Date 23/10/2003

The Design is a two stage OPAMP as per the given problem. In order to meet the power dissipation criteria the currents are also chosen as suggested. The design flow used for the 1^{st} stage and 2^{nd} stage is described below.

1st Stage

The first stage of op-amp is a differential input, single ended output with active current load. The sizes and overdrive voltages have been chosen as follows:

MB1: To support 5µA current with $V_g = 1v$, the calculated W/L was 3.5/13.5, but as observed in the results the current is half then expected, which is due to mobility degradation (since high V_{sg}) so the W/L were increased to 3.5/27.5 which gives $I_d = 5.014\mu A$.

MB2: Since Id = 5μ A and since its G and D are shorted which were also connected to gate of other (Current Mirror) transistors, so V_{gs} is chosen as 180mV which yields W/L = 11/3.5

M5: Since $I_d = 60\mu A$ and Vgs = 180mv the calculated W/L was 132/3.5 (12 times MB2), but the I_d obtained with this W/L was 64.46 μA , so W/L was reduced to 123/3.5 (which is later adjusted to 121.9/3.5 to meet offset requirement as explained later) to obtain $I_d = 59.23\mu A$.

M1, M2: This are differential pair transistors and I_d from each one is 30µA, one requirement for them is to reduce mismatch which can be done by larger W/L, the V_t is more since they are affected from body effect. Here we require the output at drain of M2 (M1) as 2.2 v in order to drive the 2nd stage so correspondingly W/L were chosen as 42/3.5.

M3, M4: In the current source load transistor also $I_d = 30\mu A$ and $V_{sg} (= V_{ds}) = 1.1v$ (M3) was chosen so sizes were calculated to be 116/3.5 But from simulation V_{sg} was 1.24V. So they were resized to 123.5/3.5.

The output voltage of this stage is taken at 2.2V to get the final output at 1.65V. After simulation it was found to be 2.077V. The gain for first stage is 184.

Transistor	W/L		$I_d(\mu A)$		$V_{gs}(V)$	$g_m(\mu A/V)$
	Calculated	Simulated	Calculated	Simulated	Simulated	Simulated
MB1	3.5/27.5	3.5/13.5	5	5.014	2.3	7.266
MB2	11/3.5	11/3.5	5	5.014	0.95	45.02
M5	132/3.5	121.9/3.5	60	58.48	0.95	470.4
M1, M2	42/3.5	42/3.5	30	29.24	1.062	222.6
M3, M4	116/3.5	123.5/3.5	30	29.24	1.244	228.7

Table-1

2nd Stage

In order to get $A_v > 2500$ the second stage needs to have a gain of at least 2500/184 > 15. The current for 2^{nd} stage is set to 30μ A. Transistor sizes:

M7: Size of M7 = 66/3.5(6 times MB2), but is sized to 57/3.5 (actually is later adjusted to make output at 1.65v)

M6: The Common Source amplifier is designed to provide $I_d = 30\mu A$, sufficient gain and $V_o=1.65v$. Firstly we simply size it to be same size to that of M6 (since Id is same for both) i.e. 116/3.5

Transistor	W/L		$I_d (\mu A)$		$V_{gs}(V)$	$g_m(\mu A/V)$
Tansistor	Calculated	Simulated	Calculated	Simulated	Simulated	Simulated
M6	116/3.5	115.5/13.5	30	29.33	1.224	229.5
M7	57/3.5	57/3.5	30	29.33	0.95	252.2

Table-2

Differential Gain, $A_{OL} = 93.71 dB (A_{vl})$	= -184 and A _{v2} $=$ -229)	
Phase Margin (PM)= - 47°	f _{3db} =34.67KHz,	$f_u = 72.44 MHz$
The poles are observed at	$p_1 = 34.67 \text{ KHz}$	$p_2 = 3.6 MHz$

Pole Splitting and Zero Cancellation:

As observed the PM was negative, to make it positive we performed pole splitting and Zero Cancellation using C_c and R_z (realized as Mz) as mentioned below:

By formula $C_c=g_{m1}/(2\pi f_u)$ where f_u is the unity gain freq. By simulation g_{m1} was 222.6µA/V. Now we can set f_u at the location of second pole (p_2) (to make the PM of A_{OL} approx 45⁰). To give a little more margin f_u was set to 3MHz. C_c was then calculated as 11.8pF. The obtained PM was quite low i.e. 1.57° with $f_u=8$ MHz. Due to presence of Zero at frequency g_{m6}/C_c , f_u of the opamp and location of the zero occur close together. Since the zero is in the right half S plane, PM is further degraded. So Zero cancellation is done using R_z in series with C_c .

The value of R_z can be approximated to $1/g_{m6}$ (where g_{m6} from simulation was 229.88 μ A/V) i.e. 4.35k. With R_z =4.35k and $C_c = 12$ pF when the PM obtained was 74.5°, which is > 45°. So we adjusted R_z and C_c as 2.5pF and 4.35k and got PM=51°.

Since R_z is realized with PMOS transistor in triode region in which the channel resistance, $R_z = 1/(\beta(V_{sg}-V_{thp}))$ so setting it to $1/g_{m6}$ (to track the inverse of g_{m6} over PVT variations), we sized Mz as the same dimensions of M6 i.e. $(W/L)_{Mz} = 116/3.5$.

To bias Mz we also need to use MB3, MB4, MB5 transistors in series, by setting I_d in MB3-5 branch = 5 μ A, the dimensions were

 $(W/L)_{MB3} = 4/3.5$ $(W/L)_{MB4} = 21.4/3.5$, $(W/L)_{MB5} = 11/3.5$. Using these values the PM obtained was 35.67°. In order to make PM > 45°, C_c and Mz were varied, so finally we got PM as 55.26° at $(W/L)_{Mz}$ =85/3.5 (Ron = 2.52k) and C_c = 12pF.

In order to meet output voltage, gain, PM the transistor sizes were frequently changed which resulted into difference in the following ratio

$$\frac{(W/L)3}{(W/L)6} = \frac{(W/L)4}{(W/L)6} = \frac{(W/L)5}{2*(W/L)7}$$

This ratio should be mate in order to minimize the systematic offset, so the transistor sizes were tuned to meet this ratio as close as possible without affecting other parameters. The final sizes of this transistors are thus as shown in the table 1.

Total I_d obtained is 97.75 μ A and Static Power Dissipation of 322.26 μ W.

1. Characterization of parameters SPICE simulation:

(A) Systematic input Offset Voltage Calculation

After tuning the transistors the output observed was 1.415V, which is less than 1.65V. So an external bias of 4.92μ V is required at Vin2 to cancel the offset voltage (This value is obtained by using Vin1=1.65V and sweeping Vin2 around this value). The frequency response remains nearly the same as in fig.4.

(*B*) The open loop differential gain versus frequency (both magnitude and phase plot) is as shown in fig.4. The open loop gain (at DC) is 93.57 dB, f_u (unity gain bandwidth) obtained is 3.14Mhz; Dominant Pole (p₁) is 63 Hz, and the PM is $180 + (-124.74) = 55.26^{\circ}$.

(*C*) The open loop common mode gain and CMRR versus frequency are plotted as shown in fig.5 and fig. 6 respectively. The $A_{OLCM}(at DC)$ is – 816.4m dB and CMRR is 94.57 dB.

(D) The poles and zeroes observed from the open loop frequency response of differential gain are as follows: $P_1 = 63 \text{ Hz}$. $Z_1 = 5.36 \text{ Mhz}$. $P_2 = 31.62 \text{ Mhz}$. $Z_2 = 316.2 \text{ Mhz}$.

As can be observed the dominant pole is at 63 Hz. And the first Zero is at a frequency greater then f_u.

(*E*) Step response of the OP-AMP for $1\mu V$ (b) 1mV, and (c) 1V are as plotted in fig.7 and fig.8. The PSRR is given in table 3. (Theoretically it should be $I_{ss}/Cc = 5V/\mu s$). It is observed that as the magnitude of step input falls the Slew Rate as drops.

Voltage	1v	1mV	1µV
SR	5.55 V/µs	23.06 mV/µs	.236µV/µs



(*F*) The Power supply noise in the OP-AMP can come either from V_{dd} or V_{ss} and it has different characteristics in the two cases. So PSRR for corresponding V⁺ and V⁻ variations on V_{dd} and V_{ss} at DC are 108.57 dB and 104.5dB. They are plotted in fig.9 and fig.10 respectively.

(G) By connecting a variable capacitance load (C_L) (in pF to nF range) at the output, PM for different C_L is noted and the minimum PM obtained by simulation is 5.3° with C_L = 1nF.

2. Comparator Circuit:

Due to V_t mismatch g_m , I_d G and D voltage of both transistors in differential pairs are not identical and hence gain is different. By fixing the V_{in1} at 1.65V and changing V_{in2} around the 1.65V offset voltage was found to be $V_{off} = 77.81212 \text{mV}(\text{exact})$. This voltage is required at V_{in2} to restore V_{out} at 1.65 for $V_{in1}=V_{in2}=1.65$ V.

(*A*) When Vin1 is varied from 0 to 3.3V, ideally V_{out} should switch to 3.3 when V_{in2} crosses 1.65 V, but due to V_t variations, V_{out} is observed to switch at 1.728V resulting into V_{off} =78mV. The V_o vs. V_{in2} plot is shown in Fig.11. The previous sweep (at +ve input around 1.65V) also what we got is confirmed from here.

(*B*) Input Series Cancellation: It is used to perform offset voltage cancellation. Here the OPAMP is used with a capacitor $C_o = 1pF$ and 3 switches realized as Pass transistors. V_{in2} varies from 0 - 3.3V, the switching is plotted and shown in Fig 12. It can observed that $V_{out} = 1.6985V$ so $V_{off} = 48.5mV$ which is less than that observed in (a) but could not be removed completely due to charge sharing and discharging of the capacitor due to delay between switching the switches.

(*C*) Output Series Cancellation: Since $A_{OL} > 93$ dB and the offset is in few mV so the capacitor have to store $A_{OL}*V_{off}$, hence the output goes into saturation and we cannot get the exact value. During the simulation output saturates and hence the offset cancellation can't be observed in this case.



Fig.4 Open Loop Freq. Response with compensation





Fig.11 Comparator Output with Vt mismatch

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Fig.12 input series cancellation for Comparator